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Form 1449*

Atty. Docket No.: 303.557US1

Serial No. 09/259,849

INFORMATION DISCLOSURE STATEMENT
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Applicant: Paul A. Farrar

Filing Date: March 1, 1999

Group: 1765

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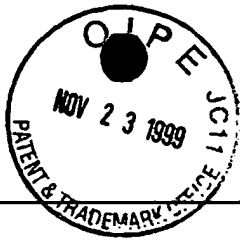
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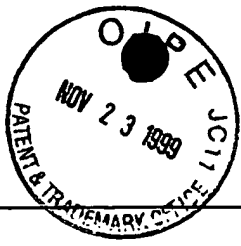
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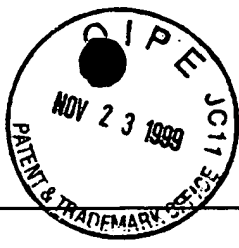
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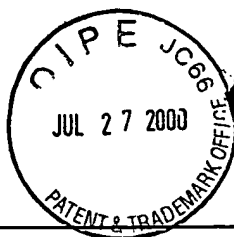
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